

IN THE CLAIMS

1. (Currently Amended) A semiconductor device fabricating method comprising the steps of:

carrying a plurality of wafers each having a plurality of chips into a die bonder and placing said plurality of wafers in said die bonder;

bonding together a plurality of chips, which is are taken out from said plurality of wafers respectively and superposed in a stack, by each bonding layer to form a chip assembly; and

bonding said chip assembly to a die pad by another bonding layer.

2. (Original) The semiconductor device fabricating method according to claim 1 further comprising the step of stacking one or a plurality of chips on said chip assembly.

3. (Original) The semiconductor device fabricating method according to claim 1 further comprising the step of stacking one or a plurality of chips on a back surface opposite a surface of said die pad to which said chip assembly is bonded.

4. (Original) The semiconductor device fabricating method according to claim 1, wherein said die bonder includes a preparatory stage having a support surface on which the chip is placed, and said support surface inhibits the adhesion of said bonding layer to said support surface.

Claims 5-7 (Cancelled)